INTEGRATED CIRCUITS



Product specification File under Integrated Circuits, IC04 January 1995



Product specification

HEF4060B MSI

14-stage ripple-carry binary counter/divider and oscillator

DESCRIPTION

The HEF4060B is a 14-stage ripple-carry binary counter/divider and oscillator with three oscillator terminals (RS, R_{TC} and C_{TC}), ten buffered outputs (O_3 to O_9 and O_{11} to O_{13}) and an overriding asynchronous master reset input (MR). The oscillator configuration allows design of either RC or crystal oscillator circuits. The oscillator may

be replaced by an external clock signal at input RS. The counter advances on the negative-going transition of RS. A HIGH level on MR resets the counter (O_3 to O_9 and O_{11} to O_{13} = LOW), independent of other input conditions.

Schmitt-trigger action in the clock input makes the circuit highly tolerant to slower clock rise and fall times.





PINNING

MR	master reset			
RS	clock input/oscillator pin			
R _{TC}	oscillator pin			
C _{TC}	external capacitor connection			
O ₃ to O ₉				
O ₁₁ to O ₁₃				

HEF4060BP(N):	16-lead DIL; plastic (SOT38-1)				
HEF4060BD(F):	16-lead DIL; ceramic (cerdip) (SOT74)				
HEF4060BT(D):	16-lead SO; plastic (SOT109-1)				
(): Package Designator North America					

FAMILY DATA, I_{DD} LIMITS category MSI

See Family Specifications



14-stage ripple-carry binary counter/divider

HEF4060B

NSI

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AC CHARACTERISTICS

 V_{SS} = 0 V; T_{amb} = 25 °C; C_L = 50 pF; input transition times \leq 20 ns

	V _{DD} V	SYMBOL	MIN.	TYP.	MAX.		TYPICAL EXTRAPOLATION FORMULA
Propagation delays							
$\text{RS} \rightarrow \text{O}_3$	5			210	420	ns	183 ns + (0,55 ns/pF) C _L
HIGH to LOW	10	t _{PHL}		80	160	ns	69 ns + (0,23 ns/pF) C _L
	15			50	100	ns	42 ns + (0,16 ns/pF) C _L
	5			210	420	ns	183 ns + (0,55 ns/pF) C_{L}
LOW to HIGH	10	t _{PLH}		80	160	ns	69 ns + (0,23 ns/pF) C _L
	15			50	100	ns	42 ns + (0,16 ns/pF) C _L
$O_n \to O_{n+1}$	5			25	50	ns	
HIGH to LOW	10	t _{PHL}		10	20	ns	
	15			6	12	ns	
	5			25	50	ns	
LOW to HIGH	10	t _{PLH}		10	20	ns	
	15			6	12	ns	
$MR\toO_n$	5			100	200	ns	73 ns + (0,55 ns/pF) C _L
HIGH to LOW	10	t _{PHL}		40	80	ns	29 ns + (0,23 ns/pF) C _L
	15			30	60	ns	22 ns + (0,16 ns/pF) C _L
Output transition	5			60	120	ns	10 ns + (1,0 ns/pF) C _L
times	10	t _{THL}		30	60	ns	9 ns + (0,42 ns/pF) C _L
HIGH to LOW	15			20	40	ns	6 ns + (0,28 ns/pF) C _L
	5			60	120	ns	10 ns + (1,0 ns/pF) C _L
LOW to HIGH	10	t _{TLH}		30	60	ns	9 ns + (0,42 ns/pF) C _L
	15			20	40	ns	6 ns + (0,28 ns/pF) C _L
Minimum clock pulse	5		120	60		ns	
width input RS	10	t _{WRSH}	50	25		ns	
HIGH	15		30	15		ns	
Minimum MR pulse	5		50	25		ns	
width; HIGH	10	t _{WMRH}	30	15		ns	
	15		20	10		ns	
Recovery time	5		160	80		ns	
for MR	10	t _{RMR}	80	40		ns	
	15		60	30		ns	
Maximum clock pulse	5		4	8		MHz	
frequency input RS	10	f _{max}	10	20		MHz	
	15		15	30		MHz	

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	V _{DD} V	TYPICAL FORMULA FOR P (μ W) ⁽¹⁾
Dynamic power dissipation	5	$700 f_i + f_o C_L V_{DD}^2$
per package	10	$3\ 300\ f_i + f_o C_L V_{DD}^2$
(P)	15	$8 900 f_i + f_o C_L V_{DD}^2$
Total power dissipation	5	$700 f_{osc} + f_{o}C_{L}V_{DD}^{2} + 2C_{t}V_{DD}^{2}f_{osc} + 690 V_{DD}$
when using the	10	$3 \ 300 \ f_{osc} \ + \ f_o C_L V_{DD}{}^2 \ + \ 2 C_t V_{DD}{}^2 f_{osc} \ + \ 6 \ 900 \ V_{DD}$
on-chip oscillator (P)	15	$8 \ 900 \ f_{osc} \ + \ f_o C_L V_{DD}^2 \ + \ 2 C_t V_{DD}^2 f_{osc} \ + \ 22 \ 000 \ V_{DD}$

Notes

1. where:

 $f_i = input frequency (MHz)$

 $f_o = output frequency (MHz)$

 C_L = load capacitance (pF)

 V_{DD} = supply voltage (V)

 C_t = timing capacitance (pF)

 f_{osc} = oscillator frequency (MHz)

RC oscillator



Timing component limitations

The oscillator frequency is mainly determined by R_tC_t , provided $R_t << R2$ and $R2C2 << R_tC_t$. The function of R2 is to minimize the influence of the forward voltage across the input protection diodes on the frequency. The stray capacitance C2 should be kept as small as possible. In consideration of accuracy, C_t must be larger than the inherent stray capacitance. R_t must be larger than the LOCMOS 'ON' resistance in series with it, which typically is 500 Ω at $V_{DD} = 5$ V, 300 Ω at $V_{DD} = 10$ V and 200 Ω at $V_{DD} = 15$ V.

The recommended values for these components to maintain agreement with the typical oscillation formula are:

$$\label{eq:ct} \begin{split} C_t &\geq 100 \text{ pF}, \text{ up to any practical value}, \\ 10 \text{ } k\Omega &\leq R_t \leq 1 \text{ } M\Omega. \end{split}$$

Typical crystal oscillator circuit

In Fig.5, R2 is the power limiting resistor. For starting and maintaining oscillation a minimum transconductance is necessary.





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 $T_{amb} = 25 \text{ °C}$ and $V_{DD} = 10 \text{ V}$.